

ABSTRACT

The present application relates to a semiconductor package. The semiconductor package includes a wiring structure. The wiring structure includes a first insulating layer, a conductive pad on the first insulating layer, a second insulating layer on the conductive pad, a through hole passing through the second insulating layer and overlapping with the conductive pad, a protruding pattern disposed on the conductive pad and located in the through hole, and an under bump metallurgy (UBM) layer that contacts the upper surface and side surface of the protruding pattern and is connected to the conductive pad. A semiconductor chip connected to the UBM layer and disposed on the wiring structure.

FIG.1